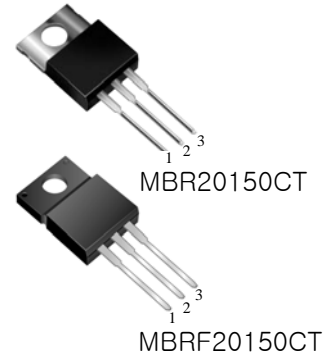




Dual SchottkyBarrierRectifiers
ReverseVoltage 150V Volts ForwardCurrent 20.0Amperes

Features

- Plastic package has underwriters Laboratory Flammability Classification 94V-0
- Dual rectifier construction, positive center tap
- Metal of silicon rectifier, majority carrier conduction
- Low forward voltage, high efficiency
- Guarding for over voltage protection
- For use in low voltage, high frequency inverters,
- Free wheeling, and polarity protection applications

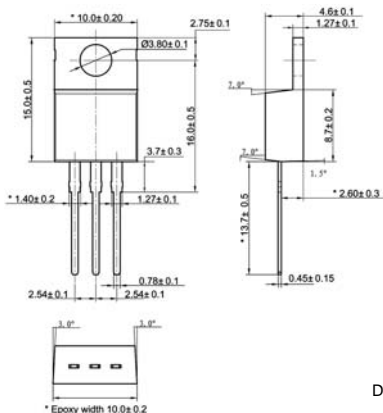


1 ANODE
2 CATHODE
3 ANODE

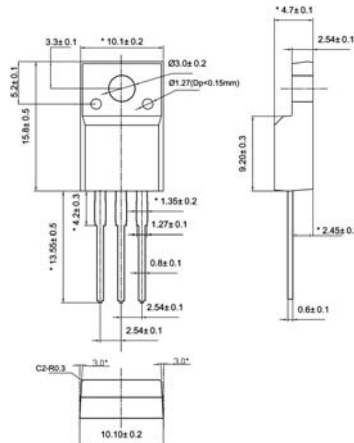
Mechanical Characteristics

- Case: Epoxy, Molded
- Weight: 1.9grams (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max.for10 sec
- Shipped 50 units per plastic tube

TO-220AB



TO-220F



Dimensions in millimeters



MBR20150CT MBRF20150CT

Maximum Ratings and Electrical Characteristics

MAXIMUM RATINGS and ELECTRICAL CHARACTERISTICS(TC=25°C unless otherwise moted)					
PARAMETER	TEST CONDITIONS		SYMBOL	MBRF20150CT	UNIT
Maximum repetitive peak reverse voltage			VRRM	150	V
Working peak reverse voltage			VRWM	150	V
Maximum DC blocking voltage			VDC	150	V
Maximum average forward rectified current at Tc=105°C total device per diode			IF(AV)	20 10	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode			IFSM	150	A
Peak repetitive reverse current per leg at tp=2.0us , 1KHz			IRRM	1.0	A
Voltage rate of change (rated VR)			DV/dt	10000	V/us
Operating junction temperature range			TJ	-55 to +150	°C
Storage temperature range			TSTG	-55 to +150	°C
Isolation voltage (TO-220F only) from terminal to heatsink t = 1 sec			VAC	1500	V
Maximum instantaneous forward voltage per leg	IF=10A IF=10A	Tc=25°C Tc=125°C	VF	0.92 0.75	V
Maximum reverse current per leg at working peak Reverse voltage			IR	0.2 6	mA

Thermal Characteristics Ta=25°C unless otherwise noted

Symbol	Parameter	Max	Unit
RθJC	Thermal Resistance, Junction to Case per Leg	4.0	°C /W
RθJA	Thermal Resistance, Junction to Ambient per Leg	62.5	°C /W

Note:

1. Screw mounting with 4-40 screw, where washer diameter is ≤4.9mm(0.19 ")
2. Pulse test:300us pulse width,1% duty cycle

Rating and Characteristic Curves Electrical Characteristics

(TA = 25 °C unless otherwise noted)

Fig. 1: Average forward power dissipation versus average forward current (per diode).

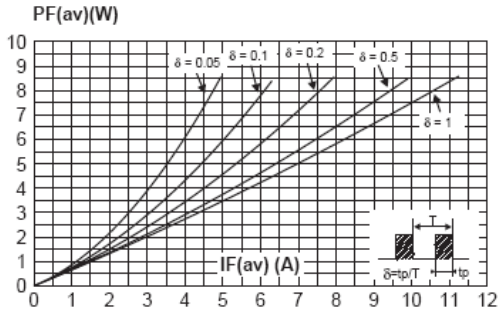


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$, per diode).

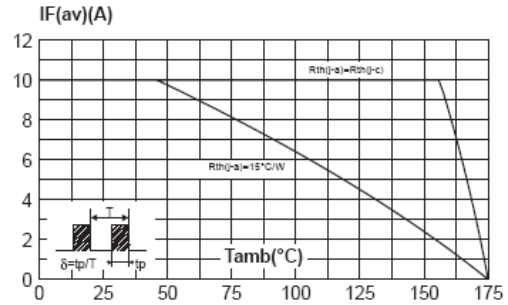


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

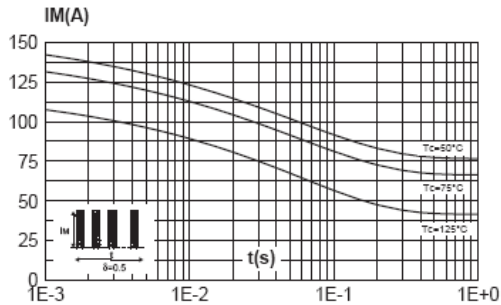


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration (per diode).

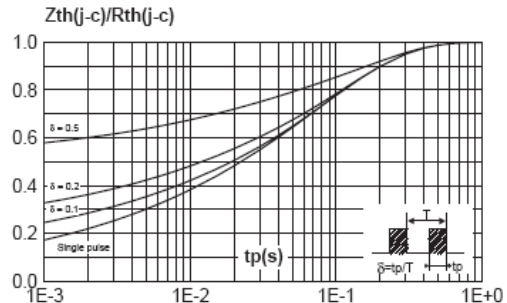


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

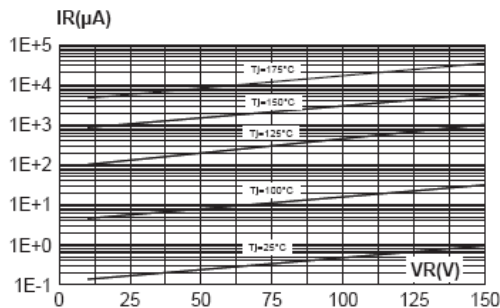


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).

